
2SK2794

Silicon N-Channel MOS FET
UHF Power Amplifier

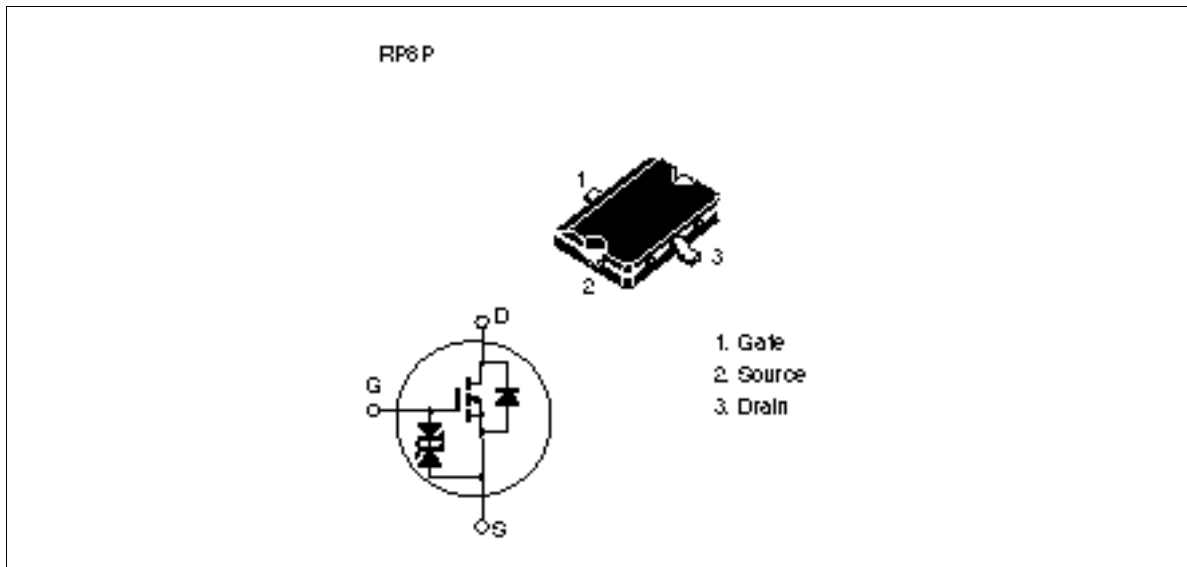
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ADE-208-465
1st. Edition

Features

- High power output, High gain, High efficiency
PG = 8.0dB, Pout = 31dBm, $\eta_D = 60\%$ min. (f = 836.5MHz)
- Compact package capable of surface mounting

Outline



This Device is sensitive to Electro Static Discharge.
An Adequate handling procedure is requested.

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	10	V
Gate to source voltage	V _{GSS}	±6	V
Drain current	I _D	0.7	A
Drain peak current	I _{D(pulse)} * ¹	1.4	A
Channel dissipation	P _{ch} * ²	3	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-45 to +150	°C

Notes: 1. PW ≤ 10ms, duty cycle ≤ 50 %

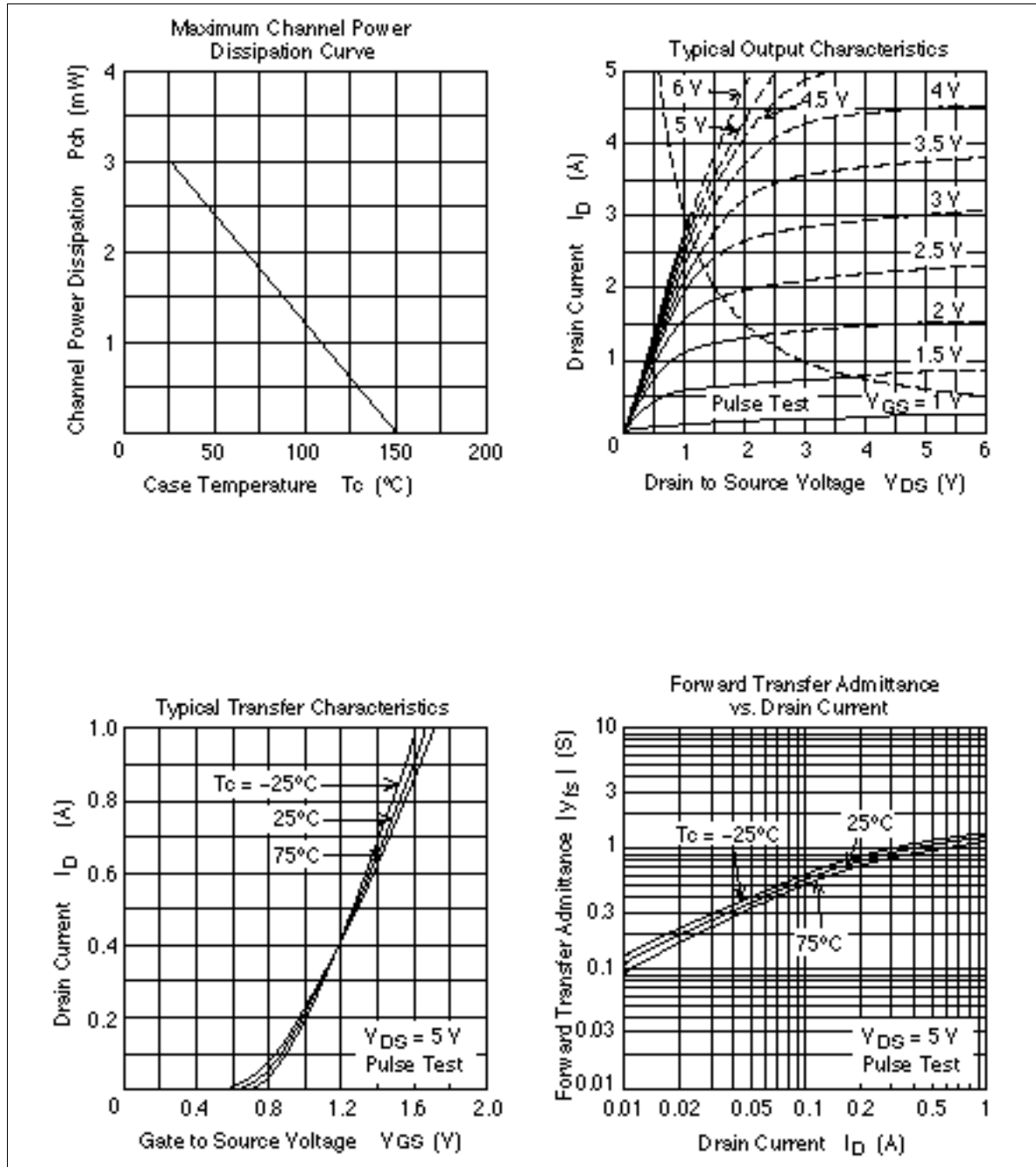
2. Value at T_c = 25°C

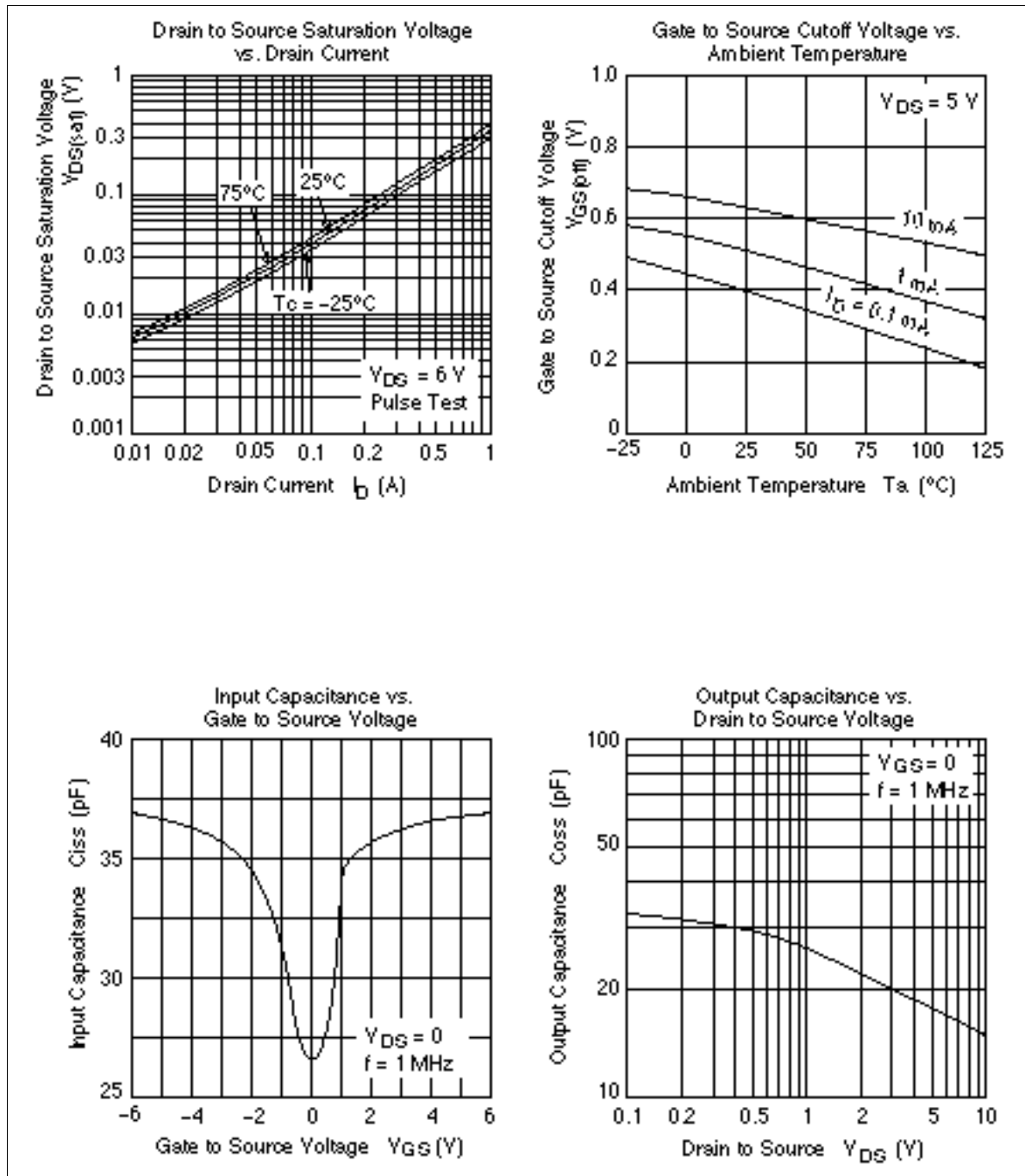
Electrical Characteristics (Ta = 25°C)

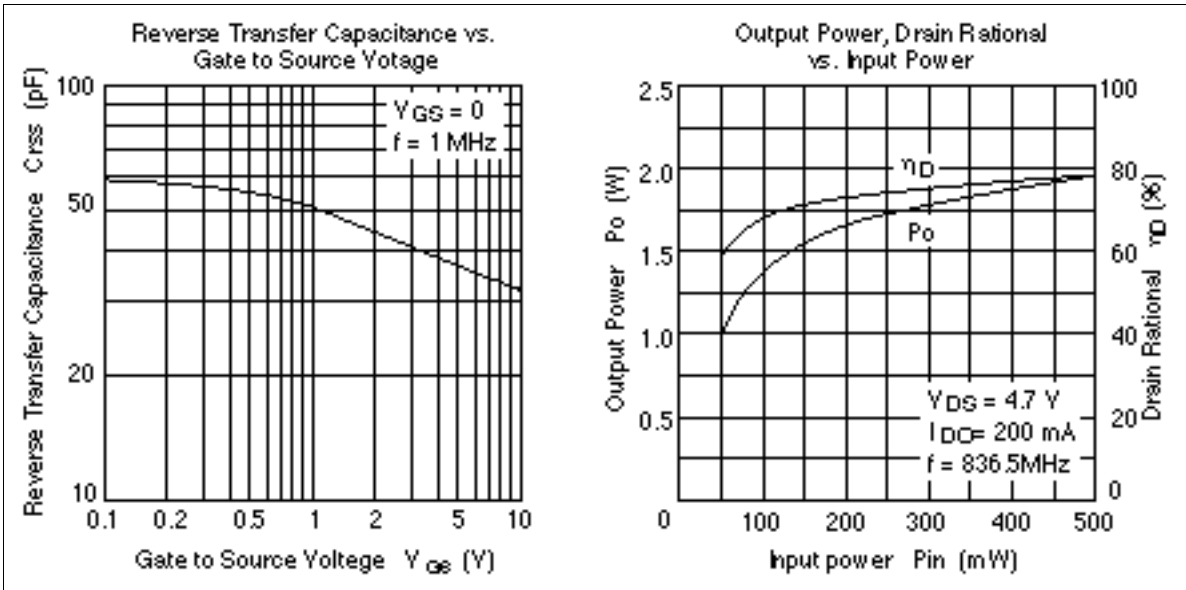
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage drain current	I _{DSS}	—	—	10	μA	V _{DS} = 10 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±5.0	μA	V _{GS} = ±6V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	1.0	—	2.0	V	I _D = 4mA, V _{DS} = 5V
Input capacitance	C _{iss}	—	36	—	pF	V _{GS} = 2V, V _{DS} = 0 f = 1MHz
Output capacitance	C _{oss}	—	17	—	pF	V _{DS} = 5, V _{GS} = 0 f = 1MHz
Output Power	P _{out}	31	—	—	dBm	V _{DS} = 4.7V f = 836.5MHz Pin = 23dBm
Drain Rational	η _D	60	—	—	%	V _{DS} = 4.7V f = 836.5MHz Pin = 23dBm

Note: 3. Marking is "CX".

Main Characteristics



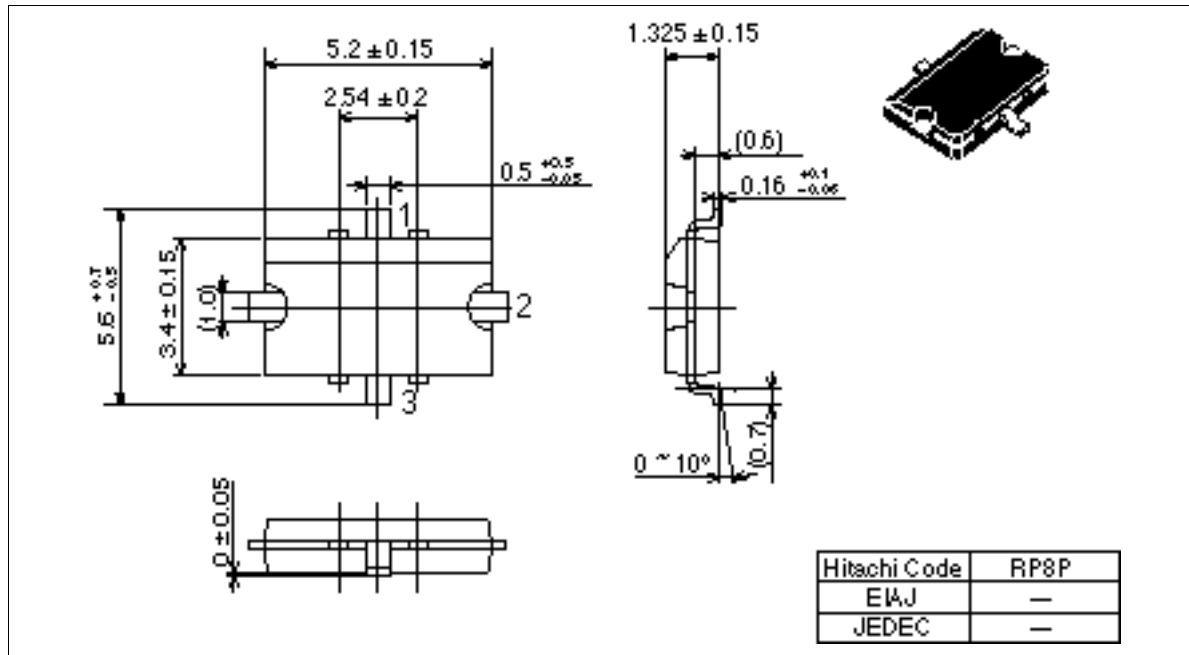




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Package Dimentions

Unit: mm



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